

**WHAT IS CLAIMED IS:**

1           1.       An electrophoretic display, comprising: a gate line that runs in a first direction;  
2           a data line that runs in a second direction; and  
3           a pixel electrode formed on an area where the gate line intersects the data line,  
4           wherein a portion of the pixel electrode overlaps a portion of the gate line.

1           2.       An electrophoretic display of claim 1,  
2           wherein a portion of the pixel electrode overlaps a portion of the data line.

1           3.       An electrophoretic display of claim 1, further comprising:  
2           an insulating layer interposed between the data line and the pixel electrode,  
3           wherein the insulating layer has a dielectric constant lower than 4.

1           4.       An electrophoretic display of claim 1,  
2           wherein the data line is made of metal such as Mo, Mo alloy, Cr, Ta and Ti.

1           5.       An electrophoretic display of claim 1, further comprising:  
2           a thin film transistor having a channel; and  
3           a source electrode;  
4           a drain electrode;  
5           wherein the pixel electrode is made of opaque material, and  
6           wherein the pixel electrode overlaps the channel of the thin film transistor.

1           6.     An electrophoretic display of claim 3,  
2           wherein the insulating layer is made of a-Si:C:O or a-Si:O:F.

1           7.     An electrophoretic display, comprising;  
2           a gate electrode;  
3           a source electrode;  
4           a drain electrode a semiconductor layer; and  
5           an opaque layer,  
6           wherein the opaque layer lies opposite to the gate electrode with the semiconductor layer  
7 disposed therebetween.

1           8.     An electrophoretic display of claim 7, further comprising:  
2           a data line; and  
3           a gate line,  
4           wherein the inclination angle of the gate line or the data line relative to the surface of the  
5 substrate ranges between about 20 degrees to about 80 degrees.

1           9.     An electrophoretic display of claim 7, further comprising:  
2           an insulating layer formed between the data line and the pixel electrode,  
3           wherein the insulating layer has a dielectric constant smaller than 4.

1           10.    An electrophoretic display of claim 7,  
2           wherein the data line is made of metal such as Mo, Mo alloy, Cr, Ta and Ti.

1 11. An electrophoretic display of claim 7, further comprising:  
2 a thin film transistor with a channel;  
3 wherein the pixel electrode is made of opaque material, and  
4 wherein the pixel electrode overlaps the channel of the thin film transistor.

1 12. An electrophoretic display of claim 9,  
2 wherein the insulating layer is made of a-Si:C:O or a-Si:O:F.

1 13. An electrophoretic display of claim 7, further comprising:  
2 a pixel electrode;  
3 a data line; and  
4 a gate line,  
5 wherein the pixel electrode overlaps the data line and the gate line.

1 14. An electrophoretic display, comprising;  
2 a substrate; and  
3 a thin film transistor that comprises  
4 a source electrode and a drain electrode formed on the substrate;  
5 a semiconductor layer formed on the source and the drain electrode;  
6 an insulation layer formed on the semiconductor layer; and  
7 a gate electrode formed on the insulation layer.

1        15.     An electrophoretic display of claim 14, further comprising:  
2        a gate line;  
3        a data line; and  
4        a pixel electrode,  
5        wherein a portion of the pixel electrode overlaps a portion of the gate line, and  
6        wherein a portion of the pixel electrode overlaps a portion of the data line.

1        16.     An electrophoretic display of claim 15,  
2        wherein an insulating layer is between the data line and the pixel electrode, and  
3        wherein the insulating layer has a dielectric constant smaller than 4.

1        17.     An electrophoretic display of claim 15,  
2        wherein the data line is made of metal such as Mo, Mo alloy, Cr, Ta and Ti.

1        18.     An electrophoretic display of claim 15,  
2        wherein the inclination angle of the gate line or the data line relative to the surface of the  
3        substrate ranges between about 20 degree to 80 degree.

1        19.     An electrophoretic display of claim 16,  
2        wherein the insulating layer is made of a-Si:C:O or a-Si:O:F.

1        20.     An electrophoretic display, comprising;  
2        a gate line;

3 a data line;  
4 a pixel electrode;  
5 a common electrode; and  
6 a plurality of micro-capsules,  
7 wherein each of the microcapsules includes electric ink containing a plurality of color  
8 pigment particles,  
9 wherein the plurality of color pigment particles are at least one of red, green, blue, cyan,  
10 yellow, magenta, black and white, and  
11 wherein a portion of the pixel electrode overlaps a portion of the gate line.

1 21. An electrophoretic display of claim 20,  
2 wherein a portion of the pixel electrode overlaps a portion of the data line.

1 22. An electrophoretic display of claim 20, further comprising:  
2 an insulating layer formed between the data line and the pixel electrode,  
3 wherein the insulating layer has a dielectric constant smaller than 4.